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METHODOLOGY FOR ANALYZING AND QUANTIFYING DESIGN STYLE CHANGES AND COMPLEXITY USING TOPOLOGICAL PATTERNS JASON CAIN¹, YA-CHIEH LAI², FRANK GENNARI², JASON SWEIS² ¹ADVANCED MICRO DEVICES, ²CADENCE DESIGN SYSTEMS





TOPOLOGICAL PATTERN DESCRIPTION

LAYOUT PATTERN EXTRACTION

TOPOLOGICAL LAYOUT COMPARISON

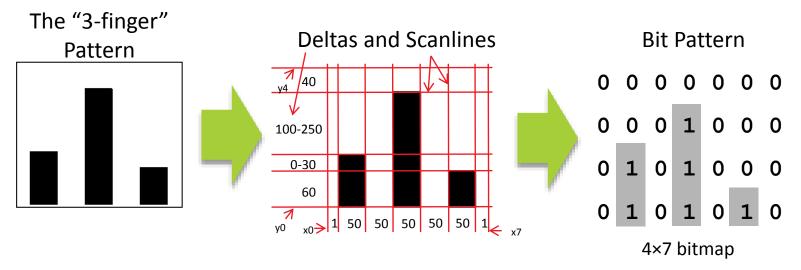
SUMMARY

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INTRODUCTION

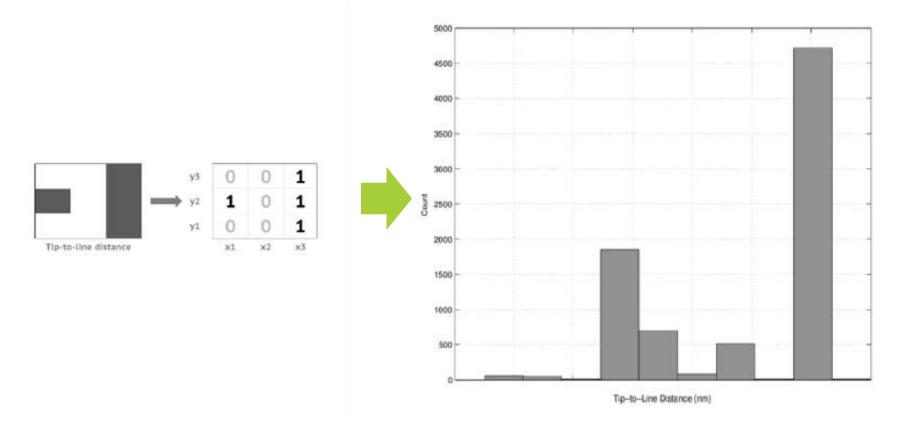
- Pattern matching engines have been available in the IC physical design ecosystem for over a decade.
- ▲ The use of pattern matching to augment design-rule checking (DRC) in the physical verification flow has been widely adopted.
- Early pattern matching engines used a three-value logic (TVL) method for describing patterns.
- The more recent introduction of topological-based pattern matching engines has opened a range of new applications for layout analysis.

TOPOLOGICAL PATTERN DESCRIPTION



- A powerful tool for characterizing and comparing physical designs
- Compact form for describing patterns
- Can be independent of physical dimensions

TOPOLOGICAL PATTERNS CAN BE USED FOR ANALYSIS



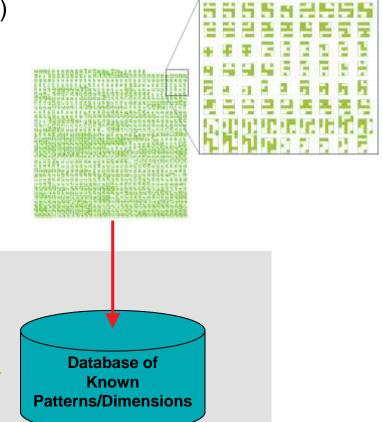
- 1. Understand usage of patterns in your designs (with locations)
- 2. Identify common cases (which must yield well) and outliers/edge cases
- 3. Identify what is new/different in an incoming design

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LAYOUT PATTERN EXTRACTION

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- 1. Systematically scan a window across entire design (choice of window size is important!)
- In every window, break-down and identify <u>every</u> pattern and sub-pattern that exists in that design (with <u>dimensions</u>)
- 3. Store a full catalog of all patterns with dimensions



▶ In our experiments, full chip 1X Metal layers captured in < 8 hours w/ 32 CPUs

Pattern

Extraction

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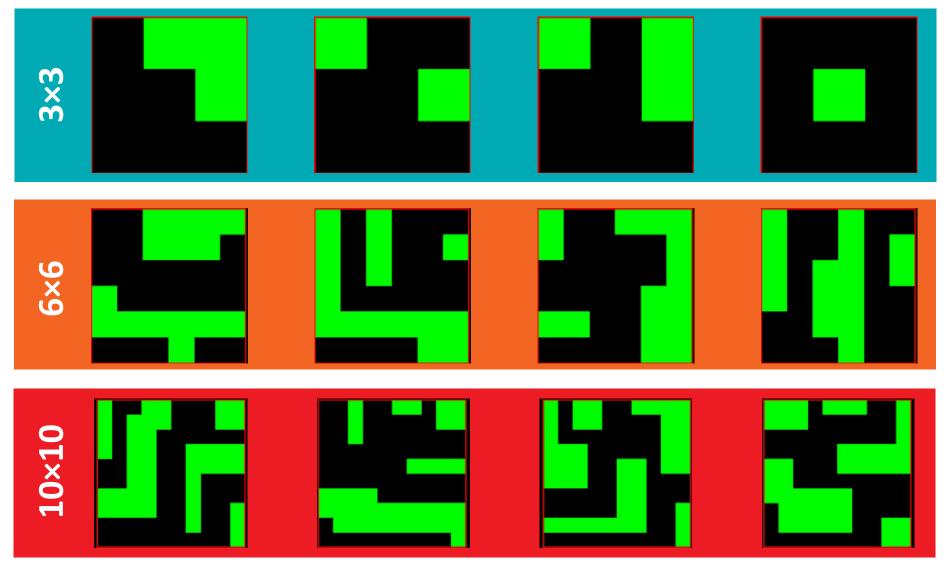
Reference

Design(s)

(OASIS,GDS)

Pattern Capture

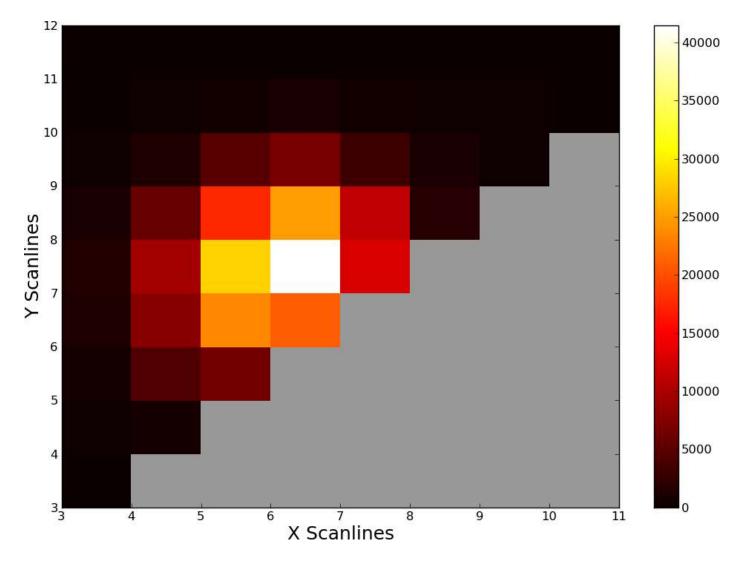
TOPOLOGICAL PATTERN EXAMPLES FOR MX LAYERS 14NM DIGITAL LOGIC – WINDOW SIZE = 3 METAL PITCHES



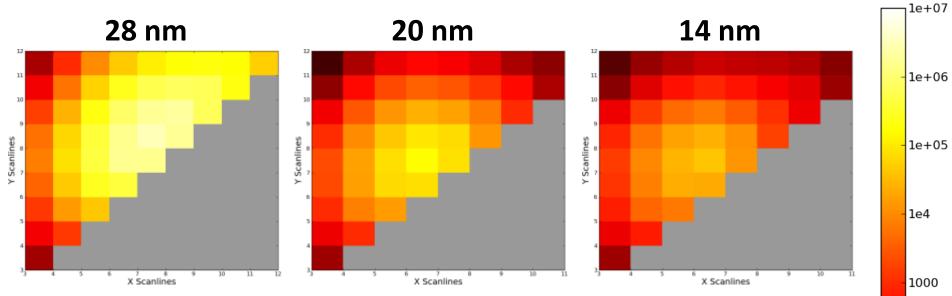
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PATTERN EXTRACTION FOR 14NM DIGITAL LOGIC 1X METAL LAYERS, WINDOW SIZE = 3 METAL PITCHES, INEXACT MATCHES



EVOLUTION OF DESIGN TOPOLOGICAL COMPLEXITY AMDIA 1X METAL LAYERS, WINDOW = 3 METAL PITCHES, INEXACT MATCHES AMDIA



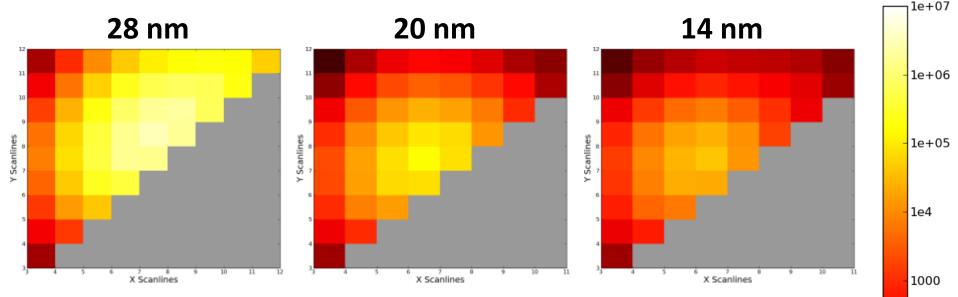
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- ▲ The same circuit was implemented in 28, 20, and 14 nm technologies.
- Pattern extraction was run on each and the number of unique topologies was counted.

Note the use of a log scale.	Technology Node	Total Unique Patterns
	28 nm	20,718,038
	20 nm	835,017
	14 nm	242,617

EVOLUTION OF DESIGN TOPOLOGICAL COMPLEXITY 1X METAL LAYERS, WINDOW = 3 METAL PITCHES, INEXACT MATCHES

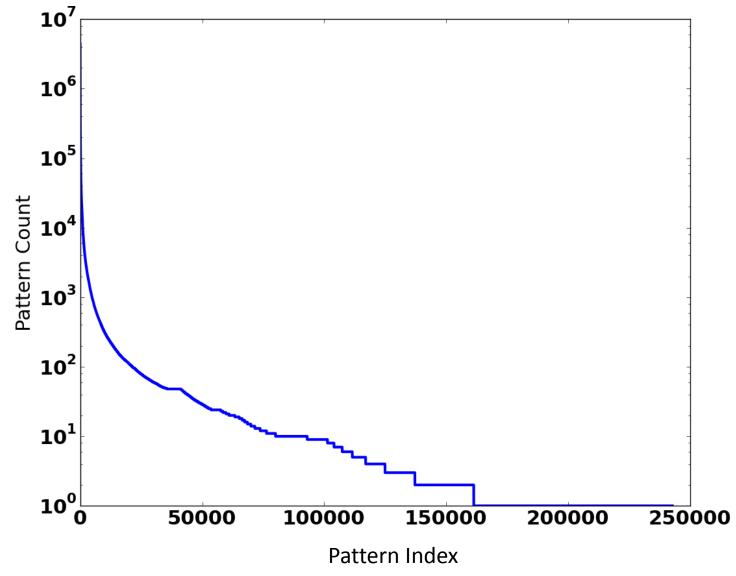


- ▲ An order of magnitude decrease in the design complexity (as measured by the number of unique topologies) of 1x metal layers from 28nm to 20nm.
 - Shift to double patterning
 - Some metal routing complexity shifted to local interconnect
- Additional decrease of ~4× from 20nm to 14nm despite the fact that 1x metal design rules are very similar.
 - Shift to FinFET devices and impact of increased regularity of front end

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DISTRIBUTION OF TOPOLOGY COUNTS 14NM DIGITAL BLOCK, 1X METAL LAYERS



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PATTERN SPACE SIZE

X	Y	Total Possible	Reduced Space*
3	3	512	38 (7%)
3	4	4,096	299 (7%)
3	5	32,768	1,716 (5%)
3	6	262,144	9,044 (3%)
3	7	2,097,152	49,610 (2%)
3	8	16,777,216	267,390 (2%)
3	9	134,217,728	1,452,652 (1%)
3	10	1,073,741,824	7,864,304 (1%)
4	4	65,536	1,900 (3%)
4	5	1,048,576	43,428 (4%)
4	6	16,777,216	479,491 (3%)
4	7	268,435,456	5,202,792 (2%)
5	5	33,554,432	500,948 (1%)

The number of possible patterns in each topological family grows very rapidly with topological complexity.

*Reduced space removes duplicates due to rotation or mirroring and non-physical patterns.

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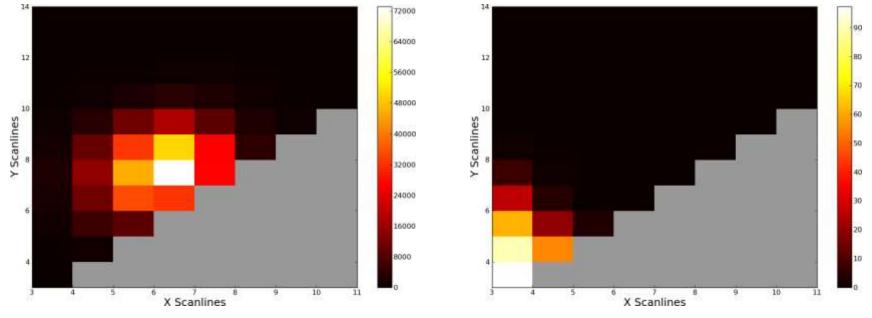
PATTERN SPACE COVERAGE 1X METAL LAYERS, WINDOW = 3 METAL PITCHES, EXACT MATCHES



Pattern Space Coverage [%]

14nm APU (CPU + GPU + Northbridge etc.) product design

Pattern Counts



- Despite the highest raw count of unique patterns occurring for pattern topologies in the 6×7 family the coverage of the total pattern space is quite low in that region.
- ▲ Pattern coverage near 100% for basic topologies (3×3) but drops off quickly.

IDENTIFICATION OF LAYOUT DIFFERENCES

Ianh overlay.oas / merged_layouts And Mundae lectron March File Windows Tools from Patro X: 434.980 Y: 401.300 marlus.me Door Data leleit fall Use cases lage firsts 40 and Rollin Identify regions where customer has 1. modified sensitive IP 2. Give OPC engineers regions that overlay.oas need more analysis Close Data Select Cell Feed forward monitoring points to 3. Open merged_lay Close Cell process teams and FA Clear Orig Hlt Layer Display 4. Give entire team an indication of Cell Display Text Display how difficult a new tape-out will be, Text on Layer Inst Property especially ramping up a new OA: overlay.oas: 99 process ■ Oas : F G Done

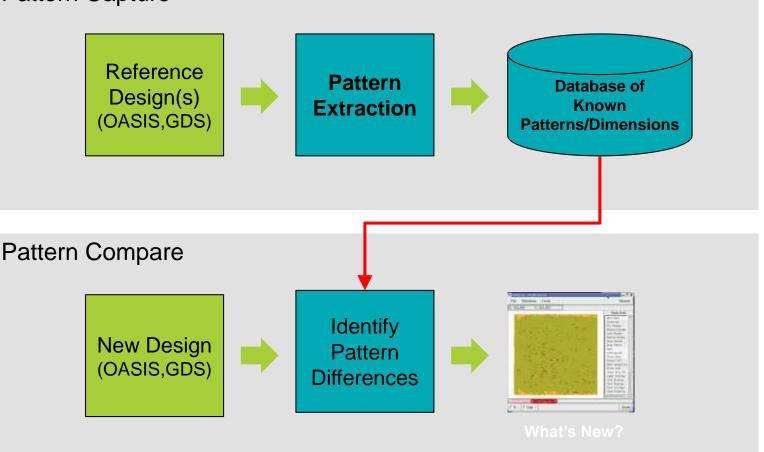
How do we define what is "new"?

- 1. Topologically Different: Patterns that have never been seen before
- 2. <u>Dimensionally Different:</u> Patterns whose dimensions are outside the range of what has been seen before

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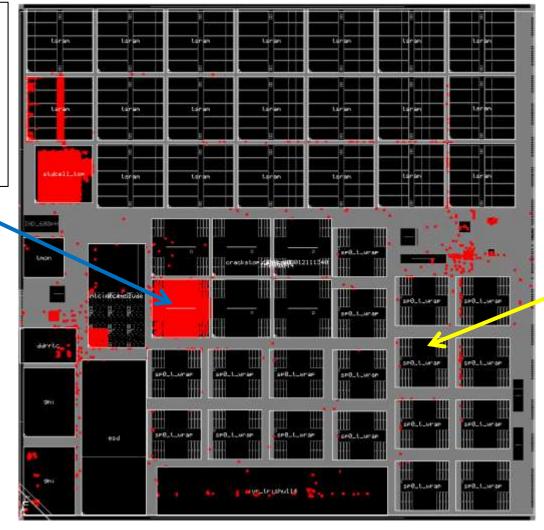
HOW CAN WE IDENTIFY WHAT IS "NEW" IN AN INCOMING DESIGN THAT WE HAVE NEVER SEEN BEFORE?

Pattern Capture



AUTOMATIC IDENTIFICATION OF REPRESENTATIVE LAYOUT DIFFERENCES

Each red point is a representative pattern present only in new design



Pattern extraction target (digital block)

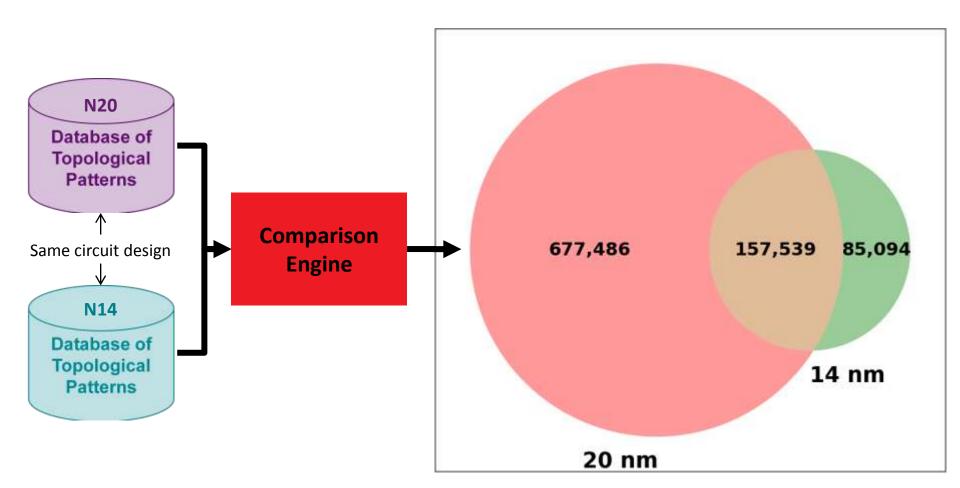
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AUTOMATIC IDENTIFICATION OF REPRESENTATIVE LAYOUT DIFFERENCES



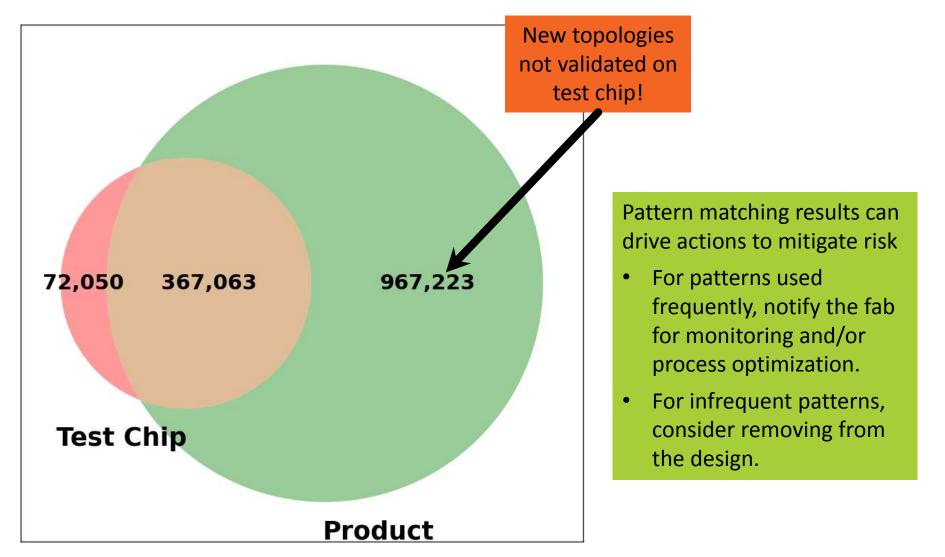
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TOPOLOGICAL DESIGN COMPARISON 1X METAL LAYERS, WINDOW SIZE = 3 METAL PITCHES, INEXACT MATCHES



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COMPARISON OF TEST CHIP TO PRODUCT TOPOLOGIES AMD



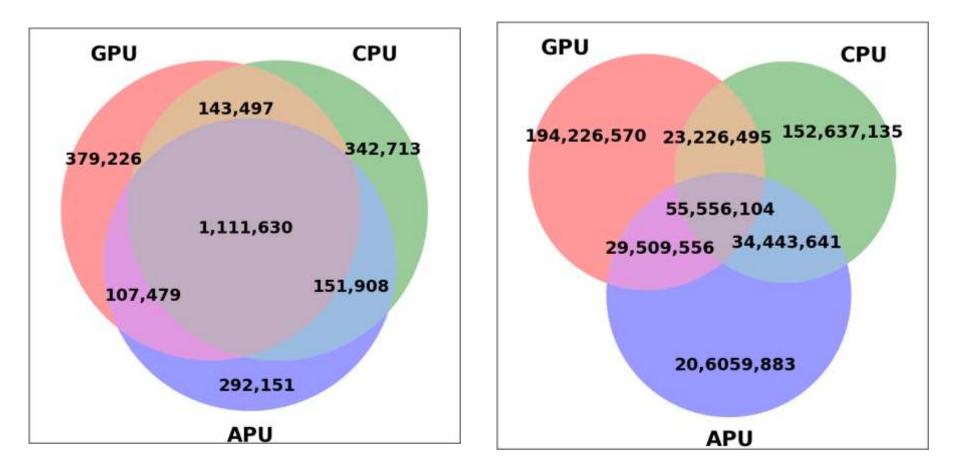
Once patterns captured, comparisons performed in < 1 hour</p>

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COMPARISON OF PRODUCT DESIGN STYLES 1X METAL LAYERS, WINDOW SIZE = 3 METAL PITCHES

Inexact matching

Exact matching



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- Topological pattern analysis provides powerful tools for measuring physical design complexity.
- Pattern extraction can be used to identify all unique pattern topologies (with or without specific dimensions) in a layout.
 - Measurable decrease in 1x metal design complexity from 28nm to 20nm to 14nm confirms that layouts are becoming more regular.
- Extracted pattern topologies can be compared between layouts to identify differences and commonalities.
 - May be used to identify potential risks and/or drive improved layout regularity.

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